

Please amend Claims 1 and 9 as follows:

1. (Amended) A method for forming a MOSFET, said method comprises:
providing a wafer, wherein said wafer comprises a substrate;
forming a trench in said substrate;
forming a gate on a bottom of said trench;
forming a spacer on both sides of said gate and filling of said trench;
implanting an ion into said substrate which is on both sides of said spacer;
proceeding a first rapid thermal process to form a source/drain region and source/drain extend region in said substrate;
forming a metal layer on said gate, said spacer, and said source/drain region;
proceeding a second rapid thermal process to said metal layer to form a silicide layer on said gate and said source/drain region; and
removing an unreacted and a remaining metal layer to remain said silicide layer on the top of said gate and on said source/drain region.

9. (Amended) A method for forming a MOSFET, said method comprises:
providing a wafer, wherein said wafer comprises a substrate;
forming a trench in said substrate;
forming a gate on a bottom of said trench, wherein said gate comprises a gate oxide layer;
forming a spacer on a sidewall of said gate and said gate oxide layer and filling of said trench;

implanting an ion into said substrate which is on both sides of said spacer;

proceeding a first rapid thermal process to form a source/drain region and a source/drain extend region in said substrate;

proceeding a second rapid thermal process to said metal layer to form a silicide layer on said gate and said source/drain region;

removing an unreacted and a remaining metal layer; and

proceeding a third rapid thermal process to said silicide layer.